

AN80xx/AN80xxM Series

3-pin, positive output, low dropout voltage regulator (50 mA type)

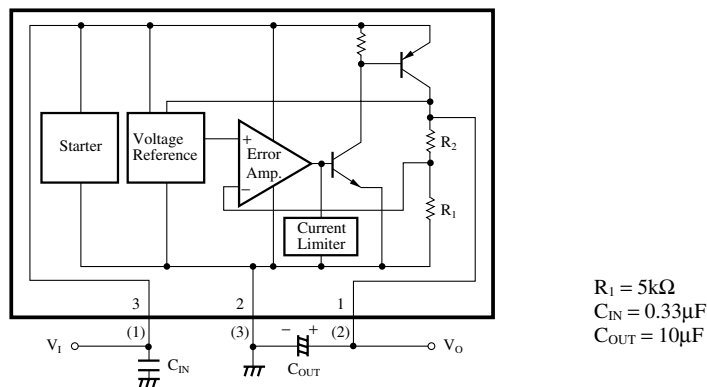
■ Overview

The AN80xx series and the AN80xxM series are 3-pin, low dropout, fixed positive output type monolithic voltage regulators. Since their power consumption can be minimized, they are suitable for battery-used power supply and reference voltage. 13 types of output voltage are available; 2.5V, 3V, 3.5V (SSIP003-P-0000 only), 4V, 4.5V and 5V.

■ Features

- Input/output voltage difference: 0.3V max.
- Output current of up to 50mA
- Low bias current: 0.6mA typ.
- Output voltage: 2.5V, 3V, 3.5V (SSIP003-P-0000 only), 4V, 4.5V and 5V.
- Built-in overcurrent protection circuit

■ Block Diagram (AN80xxM series)



Note) The number in () shows the pin number for the AN80xx series.

■ Pin Descriptions

Pin No.	Description	
	AN80xx series	AN80xxM series
1	Input	Output
2	Output	GND
3	GND	Input

■ Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Supply voltage		V_I	20	V
Supply current		I_{CC}	100	mA
Power dissipation		P_D	650 *	mW
Operating ambient temperature		T_{opr}	-30 to +80	$^\circ\text{C}$
Storage temperature	AN80xx series	T_{stg}	-55 to +150	$^\circ\text{C}$
	AN80xxM series		-55 to +125	

* AN80xxM series is mounted on standard board (glass epoxy: 20mm × 20mm × t1.7mm with Cu foil of 1cm² or more).

■ Electrical Characteristics at $T_a = 25^\circ\text{C}$

• AN8025, AN8025M (2.5V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	2.4	2.5	2.6	V
Line regulation	REG_{IN}	$V_I = 3$ to 8.5V, $T_j = 25^\circ\text{C}$	—	2.5	50	mV
Load regulation	REG_L	$I_O = 1$ to 40mA, $T_j = 25^\circ\text{C}$	—	8	20	mV
		$I_O = 1$ to 50mA, $T_j = 25^\circ\text{C}$	—	12.5	25	mV
Minimum input/output voltage difference	$V_{DIF(min)}$	$V_I = 2.4\text{V}$, $I_O = 20\text{mA}$, $T_j = 25^\circ\text{C}$	—	0.07	0.2	V
		$V_I = 2.4\text{V}$, $I_O = 50\text{mA}$, $T_j = 25^\circ\text{C}$	—	0.12	0.3	V
Bias current	I_{Bias}	$I_O = 0\text{mA}$, $T_j = 25^\circ\text{C}$	—	0.6	1	mA
Ripple rejection ratio	RR	$V_I = 3.5$ to 5.5V, $f = 120\text{Hz}$	60	72	—	dB
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	65	—	μV
Output voltage temperature coefficient	$\Delta V_O/T_a$	$T_j = -30$ to $+125^\circ\text{C}$	—	0.13	—	mV/ $^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = 3.5\text{V}$, $I_O = 20\text{mA}$ and $C_O = 10\mu\text{F}$.

• AN8003, AN8003M (3V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	2.88	3	3.12	V
Line regulation	REG_{IN}	$V_I = 3.5$ to 9V, $T_j = 25^\circ\text{C}$	—	3	50	mV
Load regulation	REG_L	$I_O = 1$ to 40mA, $T_j = 25^\circ\text{C}$	—	9	25	mV
		$I_O = 1$ to 50mA, $T_j = 25^\circ\text{C}$	—	15	30	mV
Minimum input/output voltage difference	$V_{DIF(min)}$	$V_I = 2.9\text{V}$, $I_O = 20\text{mA}$, $T_j = 25^\circ\text{C}$	—	0.07	0.2	V
		$V_I = 2.9\text{V}$, $I_O = 50\text{mA}$, $T_j = 25^\circ\text{C}$	—	0.12	0.3	V
Bias current	I_{Bias}	$I_O = 0\text{mA}$, $T_j = 25^\circ\text{C}$	—	0.6	1	mA
Ripple rejection ratio	RR	$V_I = 4$ to 6V, $f = 120\text{Hz}$	58	70	—	dB
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	70	—	μV
Output voltage temperature coefficient	$\Delta V_O/T_a$	$T_j = -30$ to $+125^\circ\text{C}$	—	0.15	—	mV/ $^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = 4\text{V}$, $I_O = 20\text{mA}$ and $C_O = 10\mu\text{F}$.

■ Electrical Characteristics at $T_a = 25^\circ\text{C}$ (continued)

• AN8035(3.5V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	3.36	3.5	3.64	V
Line regulation	REG_{IN}	$V_I = 4 \text{ to } 9.5\text{V}, T_j = 25^\circ\text{C}$	—	3.5	50	mV
Load regulation	REG_{L}	$I_O = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	10	30	mV
		$I_O = 1 \text{ to } 50\text{mA}, T_j = 25^\circ\text{C}$	—	20	40	mV
Minimum input/output voltage difference	$V_{\text{DIF}(\text{min})}$	$V_I = 3.4\text{V}, I_O = 20\text{mA}, T_j = 25^\circ\text{C}$	—	0.07	0.2	V
		$V_I = 3.4\text{V}, I_O = 50\text{mA}, T_j = 25^\circ\text{C}$	—	0.12	0.3	V
Bias current	I_{Bias}	$I_O = 0\text{mA}, T_j = 25^\circ\text{C}$	—	0.6	1	mA
Ripple rejection ratio	RR	$V_I = 4.5 \text{ to } 6.5\text{V}, f = 120\text{Hz}$	57	69	—	dB
Output noise voltage	V_{no}	$f = 10\text{Hz to } 100\text{kHz}$	—	75	—	μV
Output voltage temperature coefficient	$\Delta V_O/T_a$	$T_j = -30 \text{ to } +125^\circ\text{C}$	—	0.2	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = 4.5\text{V}$, $I_O = 20\text{mA}$ and $C_O = 10\mu\text{F}$.

• AN8004, AN8004M (4V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	3.84	4	4.16	V
Line regulation	REG_{IN}	$V_I = 4.5 \text{ to } 10\text{V}, T_j = 25^\circ\text{C}$	—	3.5	50	mV
Load regulation	REG_{L}	$I_O = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	10	30	mV
		$I_O = 1 \text{ to } 50\text{mA}, T_j = 25^\circ\text{C}$	—	20	40	mV
Minimum input/output voltage difference	$V_{\text{DIF}(\text{min})}$	$V_I = 3.8\text{V}, I_O = 20\text{mA}, T_j = 25^\circ\text{C}$	—	0.07	0.2	V
		$V_I = 3.8\text{V}, I_O = 50\text{mA}, T_j = 25^\circ\text{C}$	—	0.12	0.3	V
Bias current	I_{Bias}	$I_O = 0\text{mA}, T_j = 25^\circ\text{C}$	—	0.6	1	mA
Ripple rejection ratio	RR	$V_I = 5 \text{ to } 7\text{V}, f = 120\text{Hz}$	56	67	—	dB
Output noise voltage	V_{no}	$f = 10\text{Hz to } 100\text{kHz}$	—	80	—	μV
Output voltage temperature coefficient	$\Delta V_O/T_a$	$T_j = -30 \text{ to } +125^\circ\text{C}$	—	0.2	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = 5\text{V}$, $I_O = 20\text{mA}$ and $C_O = 10\mu\text{F}$.

• AN8045, AN8045M (4.5V type)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	4.32	4.5	4.68	V
Line regulation	REG_{IN}	$V_I = 5 \text{ to } 10.5\text{V}, T_j = 25^\circ\text{C}$	—	4	50	mV
Load regulation	REG_{L}	$I_O = 1 \text{ to } 40\text{mA}, T_j = 25^\circ\text{C}$	—	11	35	mV
		$I_O = 1 \text{ to } 50\text{mA}, T_j = 25^\circ\text{C}$	—	23	45	mV
Minimum input/output voltage difference	$V_{\text{DIF}(\text{min})}$	$V_I = 4.3\text{V}, I_O = 20\text{mA}, T_j = 25^\circ\text{C}$	—	0.07	0.2	V
		$V_I = 4.3\text{V}, I_O = 50\text{mA}, T_j = 25^\circ\text{C}$	—	0.12	0.3	V
Bias current	I_{Bias}	$I_O = 0\text{mA}, T_j = 25^\circ\text{C}$	—	0.7	1	mA
Ripple rejection ratio	RR	$V_I = 5.5 \text{ to } 7.5\text{V}, f = 120\text{Hz}$	54	66	—	dB
Output noise voltage	V_{no}	$f = 10\text{Hz to } 100\text{kHz}$	—	85	—	μV
Output voltage temperature coefficient	$\Delta V_O/T_a$	$T_j = -30 \text{ to } +125^\circ\text{C}$	—	0.23	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = 5.5\text{V}$, $I_O = 20\text{mA}$ and $C_O = 10\mu\text{F}$.

■ Electrical Characteristics at $T_a = 25^\circ\text{C}$ (continued)

• AN8005, AN8005M (5V type)

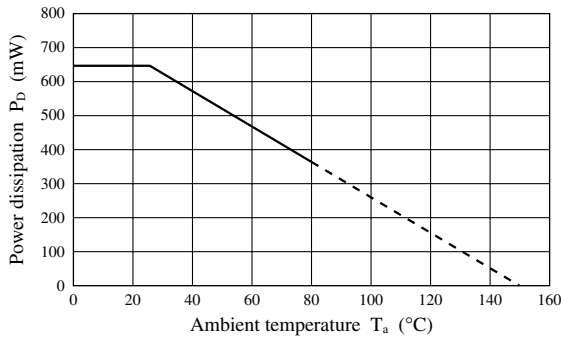
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Output voltage	V_O	$T_j = 25^\circ\text{C}$	4.8	5	5.2	V
Line regulation	REG_{IN}	$V_I = 5.5$ to 11V , $T_j = 25^\circ\text{C}$	—	4.5	50	mV
Load regulation	REG_L	$I_O = 1$ to 40mA , $T_j = 25^\circ\text{C}$	—	12	40	mV
		$I_O = 1$ to 50mA , $T_j = 25^\circ\text{C}$	—	25	50	mV
Minimum input/output voltage difference	$V_{\text{DIF}(\text{min})}$	$V_I = 4.8\text{V}$, $I_O = 20\text{mA}$, $T_j = 25^\circ\text{C}$	—	0.07	0.2	V
		$V_I = 4.8\text{V}$, $I_O = 50\text{mA}$, $T_j = 25^\circ\text{C}$	—	0.12	0.3	V
Bias current	I_{Bias}	$I_O = 0\text{mA}$, $T_j = 25^\circ\text{C}$	—	0.7	1	mA
Ripple rejection ratio	RR	$V_I = 6$ to 8V , $f = 120\text{Hz}$	52	64	—	dB
Output noise voltage	V_{no}	$f = 10\text{Hz}$ to 100kHz	—	95	—	μV
Output voltage temperature coefficient	$\Delta V_O/T_a$	$T_j = -30$ to $+125^\circ\text{C}$	—	0.25	—	$\text{mV}/^\circ\text{C}$

Note 1) The specified condition $T_j = 25^\circ\text{C}$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

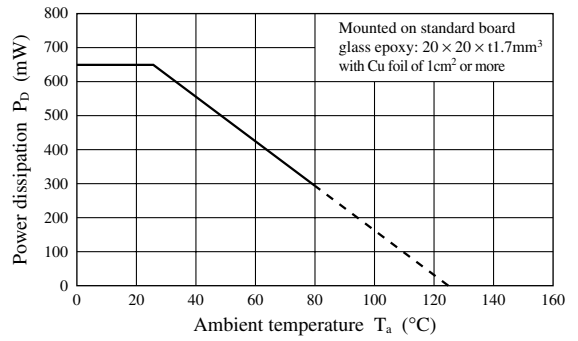
Note 2) Unless otherwise specified, $V_I = 6\text{V}$, $I_O = 20\text{mA}$ and $C_O = 10\mu\text{F}$.

■ Main Characteristics

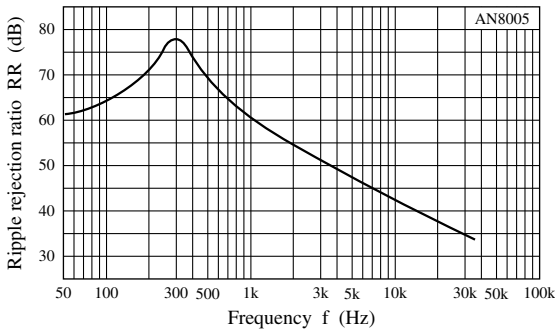
P_D — T_a (AN80xx series)



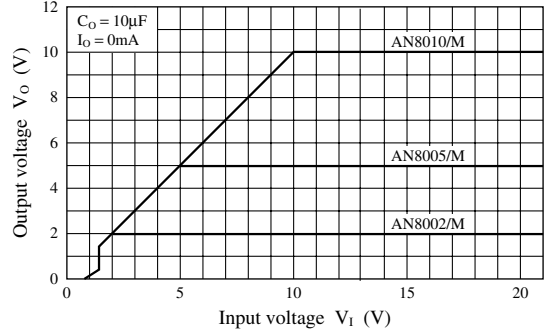
P_D — T_a (AN80xxM series)



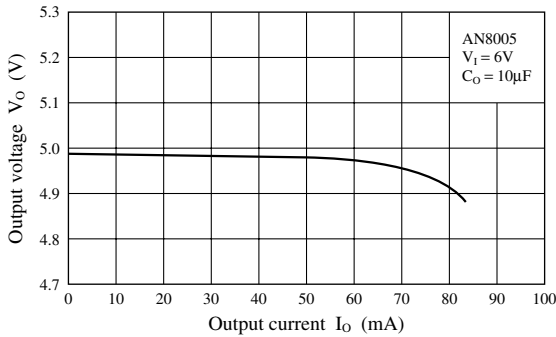
RR — f



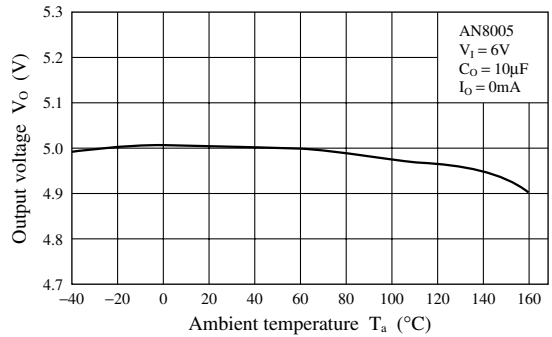
V_O — V_I



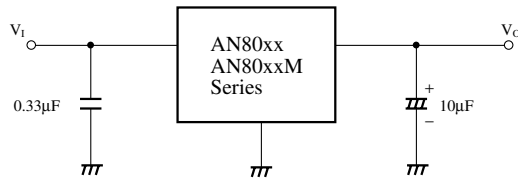
V_O — I_O



V_O — T_a



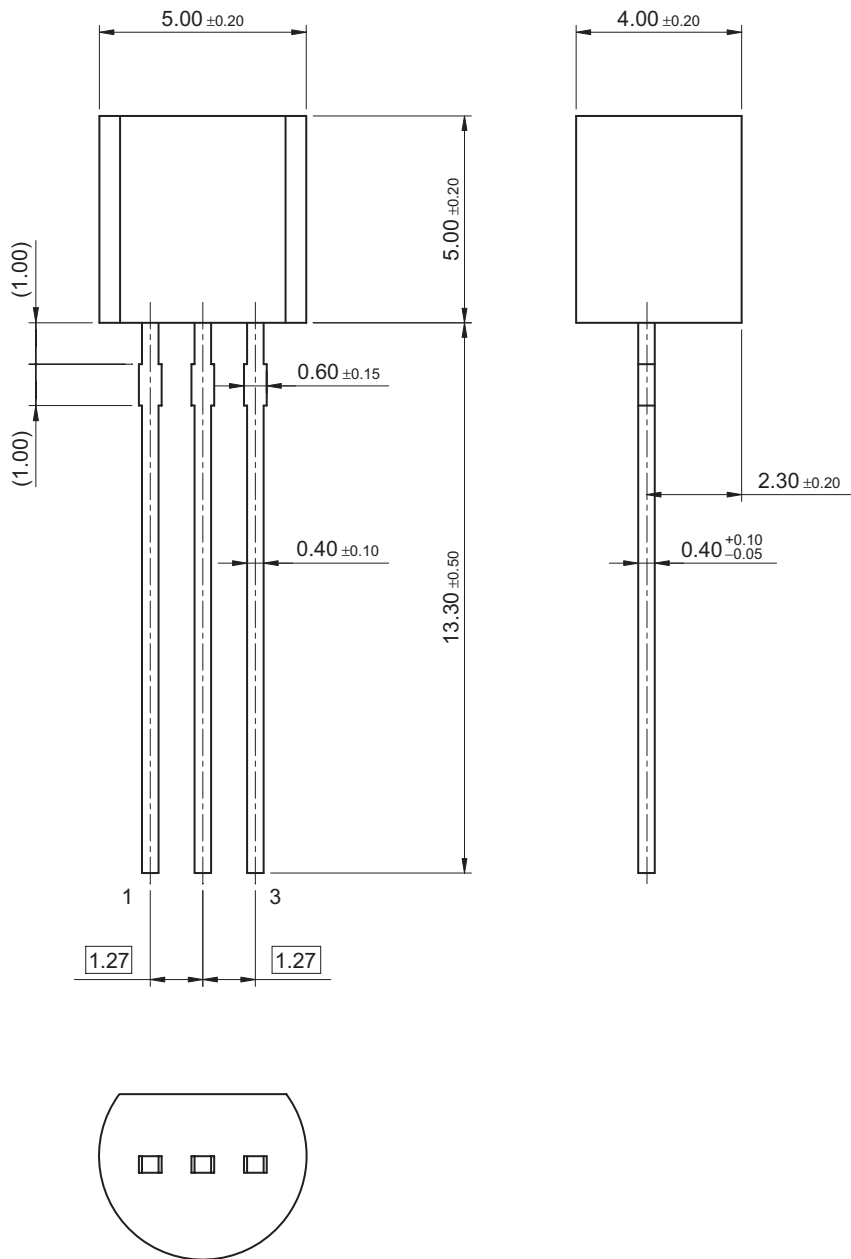
■ Application Circuit Example



- AN80xx and AN80xxM series have their internal gain increased in order to improve performance. When the power line on the output side is long, use a capacitor of $10\mu\text{F}$. Also, the capacitor on the output side should be attached as close to the IC as possible.
- When using at a low temperature, it is recommended to use the capacitors with low internal impedance (for example, tantalum capacitor) for output capacitors.

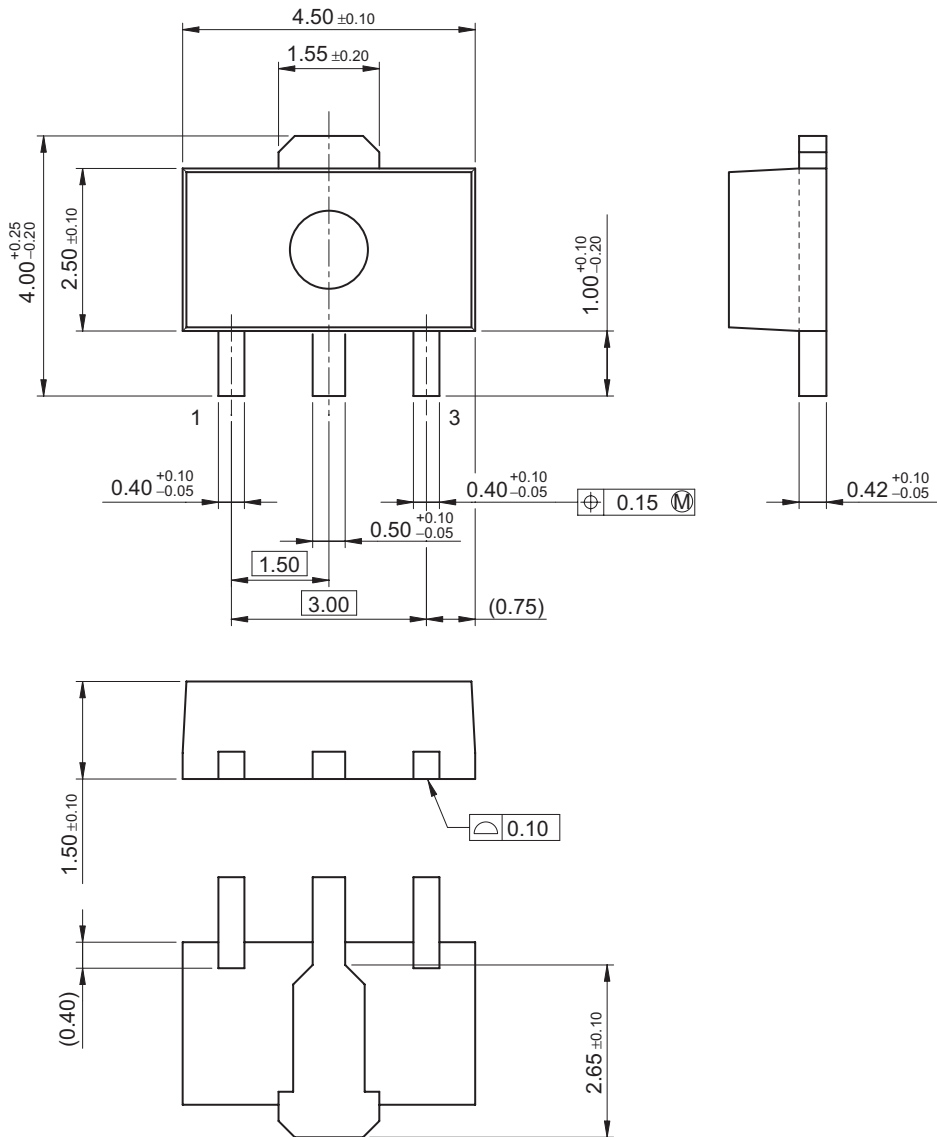
■ Package Dimensions (Unit: mm)

- SSIP003-P-0000S



■ Package Dimensions (Unit: mm)

- HSIP003-P-0000Q



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